

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

DOUGLAS S. MCGREGOR, ET AL

Serial No.: 10/695,019

Filed: October 29, 2003

For: HIGH-EFFICIENCY NEUTRON DETECTORS AND  
METHODS OF MAKING SAME

Attorney Docket No.: UOM 0316 PUSP



Group Art Unit: 2878

Examiner:

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
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Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and § 1.97-1.98, the references listed and identified on the attached Forms PTO/SB08A and/or SB08B are being submitted herewith for consideration by the Examiner.

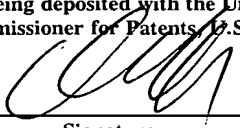
While this Statement is being filed in compliance with the duty of disclosure, citation of the attached references is not to be construed as an admission that any of the reference(s) are "material" as defined under 37 C.F.R. § 1.56(b).

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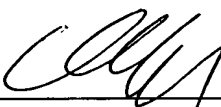
David R. Syrowik  
Name of Person Signing

  
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If the filing date of this application is on or before June 30, 2003, a copy of each reference listed on the attached Forms PTO/SB08A and/or SB08B is included herewith. If this application was filed after June 30, 2003, copies of any cited U.S. patent/application references have not been included. Consideration and entry into the record of these references is respectfully requested.

Respectfully submitted,

**DOUGLAS S. MCGREGOR, ET AL.**

By:   
David R. Syrowik  
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Date: March 31, 2004

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<b>Application Number</b>	10/695,019
<b>Filing Date</b>	October 29, 2003
<b>First Named Inventor</b>	Douglas S. McGregor, et al.
<b>Group Art Unit</b>	2878
<b>Examiner Name</b>	
<b>Attorney Docket Number</b>	UOM 0316 PUSP

Sheet 1 of 4

[illegible][illegible]Date  
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<sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Sheet	2	of	4	Attorney Docket Number	UOM 0316 PUSP

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		MCGREGOR, DOUGLAS S., ET AL., Semi-Insulating Bulk GaAs Thermal Neutron Imaging Arrays, IEEE Transactions on Nuclear Science, Vol. 43, No. 3, June 1996, pp. 1357-1364	
		ROSE, A., Sputtered Boron Films on Silicon Surface Barrier Detectors, Nuclear Instruments and Methods, 52, 1967, pp. 166-170	
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		KNOLL, GLENN F., Radiation Detection and Measurement, 3 <sup>rd</sup> Ed. John Wiley & Sons, Inc., New York, 2000, Chapter 14, pp. 505-508	
		GARBER, D.I., ET AL., Neutron Cross Sections, 3 <sup>rd</sup> Edition, Vol. 11, Curves, Brookhaven National Laboratory, Upton, January 1976, pp. 11-13 & pp. 23-24	
		MCLANE, VICTORIA, ET AL., Neutron Cross Sections, Vol. 2, Neutron Cross Section Curves, Academic Press, San Diego, CA, 1988, pp. 12-13 & pp. 26-27	
		MCGREGOR, DOUGLAS, S., ET AL., Thin-Film-Coated Bulk GaAs Detectors for Thermal and Fast Neutron Measurements, Nuclear Instruments and Methods in Physics Research A 466, 2001, pp. 126-141	
		MCGREGOR, DOUGLAS, S., ET AL., Design Considerations for Thin Film Coated Semiconductor Thermal Neutron Detectors -- I: Basics Regarding Alpha Particle Emitting Neutron Reactive Films, Nuclear Instruments & Methods, A 500, 2003, pp. 272-308	

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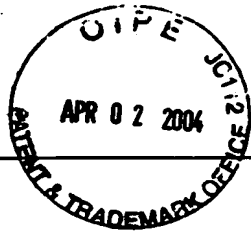
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		PUCKETT, P.R., ET AL., Thin Film Processes II, Chapter V-2, J.L. Vossen and W. Kern, Eds., Academic Press, Boston, 1991, pp. 749	
		SZE, S.M., VLSI Technology, McGraw-Hill, New York, 1983	
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		KLANN RAYMOND T., ET AL., Development of Coated Gallium Arsenide Neutron Detectors, Conference Record of ICONE-8, 8 <sup>TH</sup> International Conf. on Nuclear Eng., April 2-6, 2000, Baltimore, MD, pp. 1-6	
		MCGREGOR, DOUGLAS, S., ET AL., New Surface Morphology for Low Stress Thin-Film-Coated Thermal Neutron Detectors, IEE Transactions on Nuclear Science, Vol. 49, No. 4, August 2002, pp. 1999-2004	
		<a href="http://www.mems-exchange.org/">http://www.mems-exchange.org/</a>	
		<a href="http://physics.nist.gov/MajResProj/rfcell/drawings.html">http://physics.nist.gov/MajResProj/rfcell/drawings.html</a>	
		SCHULTEN, J., ET AL., A New Neutron Detector Development Based on Silicon Semiconductor and LiF Converter, Physica B 234-236, 1997, pp. 1084-1086	
		ATOMNAYA ENERGIYA, Soviet Atomic energy, Russian Original, Vol. 62, No. 4, April 1987, pp. 316-319	

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		ALLIER C.P., Micromachined Si-Well Scintillator Pixel Detectors, Chapter 8, 2001, pp. 122-134	

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